

100V P-CHANNEL MOSFET



Trench Power LV MOSFET Technology: Enhances performance with reduced gate drive requirements and high-efficiency operation

- and high-efficiency operation.
 Low On-Resistance: Boosts overall efficiency thanks to minimal voltage drop and heat generation during operation.
- Low Conduction Losses: Increases energy savings and improves thermal performance in power applications.
- Compact DFN3333 Package: Enables smaller, more innovative electronic designs.



On-resistance of only 85mΩ and low conduction losses ensure this MOSFET reduces energy waste and operational costs.

Trench power LV MOSFET technology minimizes heat generation, enhancing thermal management, reliability, and longevity of essential components.

Applications







Power distribution units (PDUs) Fuel cell Robotics power control units supply systems

100V P-Channel MOSFET with Trench Power LV Technology



Features Low RDS(on) & -14A Drain Current

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Space-Saving DFN3333 Package



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Product Attributes, Parametrics & Datasheets

Product	Туре	Package	Drain- Source Voltage VDS	Drain- SourceOn- Resistance RDS(on)	Continuous Drain CurrentID	Total Power Dissipation PD	Mounting Type	Datasheet
<u>MCG085P10</u>	P-Channel MOSFET	DFN3333	-100V	85mΩ	-14A	34.7W	Surface- Mount (SMD)	<u>Info</u>

Applications:



